TOSHIBA Multichip Discrete Device

HN7G08FE

General-Purpose Amplifier Applications Switching and Muting Switch Applications

Q1

Low saturation voltage: $V_{CE (sat)} (1) = -15 \text{ mV (typ.)}$

 $@I_C = -10 \text{ mA/I}_B = -0.5 \text{ mA}$

Large collector current: I_C = -400 mA (max)

Q1: 2SA1955F Q2: RN1106F

Q1 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V _{CBO}	-15	V
Collector-emitter voltage	V _{CEO}	-12	V
Emitter-base voltage	V _{EBO}	-5	V
Collector current	IC	-400	mA
Base current	I _B	-50	mA

1. EMITTER1 (E1) 90 1 2 3 COLLECTOR2(C2) 4. EMITTER2 (E2) 5. BASE2 (B2) 6. COLLECTOR1(C1) ES6 JEDEC — JEITA — TOSHIBA 2-2J1E

Weight: 0.003 g (typ.)

Q2 Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	50	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EBO}	5	V
Collector current	IC	100	mA

Q1, Q2 Common Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Collector power dissipation	P _C *	100	mW
Junction temperature	Tj	150	°C
Storage temperature range	T _{stg}	−55~150	°C

^{*} Total rating.

Q1 Electrical Characteristics (Ta = 25°C)

Characte	eristic	Symbol	Test Circuit	Test Condition		Тур.	Max	Unit
Collector cutoff cu	rrent	I _{CBO}	_	V _{CB} = -15 V, I _E = 0	_	_	-100	nA
Emitter cutoff curr	ent	I _{EBO}	_	V _{EB} =– 5 V, I _C = 0	_	_	-100	nA
DC current gain	(Note)	h _{FE}	_	V _{CE} =- 2 V, I _C =- 10 mA	300	_	1000	
Collector-emitter saturation voltage		V _{CE(sat) (1)}	_	I _C =- 10 mA, I _B =- 0.5 mA	_	-15	-30	mV
		V _{CE(sat) (2)}	_	I _C =- 200 mA, I _B =- 10 mA	_	-110	-250	IIIV
Base-emitter satur	ration voltage	V _{BE(sat)}	_	I _C =- 200 mA, I _B =- 10 mA		-0.87	-1.2	V
Transition frequency		f _T	_	V _{CE} =- 2 V, I _C =- 10 mA	_	130	_	MHz
Collector output capacitance		C _{ob}	_	V _{CB} =- 10 V, I _E = 0, f = 1 MHz	_	4.2	_	pF
Switching time Storage time Fall time	t _{on}	_	OUTPUT 300Ω OUTPUT		40	_		
	Storage time	t _{stg}	_	10μs 10μs VBB VCC = 3V = -6V		280		ns
	Fall time	t _f	_	$I_{B1} = -I_{B2} = 5 \text{ mA}$		65		

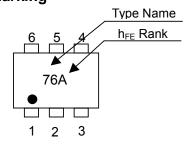
Note: h_{FE} classification A(A): 300~600, B(B): 500~1000

() marking symbol

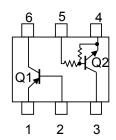
Q2 Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
Collector cutoff current	I _{CBO}	_	V _{CB} = 50 V, I _E = 0	_	_	100	nA
	I _{CEO}	_	$V_{CE} = 50 \text{ V}, I_B = 0$	_		500	IIA
Emitter cutoff current	I _{EBO}	_	V _{EB} = 5 V, I _C = 0	0.074	_	0.138	mA
DC current gain	h _{FE}	_	V _{CE} = 5 V, I _C = 10 mA	80	_	_	
Collector-emitter saturation voltage	V _{CE(sat)}	_	$I_C = 5 \text{ mA}, I_B = 0.25 \text{ mA}$	_	0.1	0.3	V
Input voltage (ON)	V _{I (ON)}	_	V _{CE} = 0.2 V, I _C = 5 mA	0.7	_	1.3	٧
Input voltage (OFF)	VI (OFF)	_	V _{CE} = 5 V, I _C = 0.1 mA	0.5		0.8	V
Transition frequency	f _T	_	V _{CE} = 10 V, I _C = 5 mA	_	250	_	MHz
Collector output capacitance	C _{ob}	_	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	3	_	pF
Input resistor	R1	_	_	3.29	4.7	6.11	kΩ
Resistor ratio	R1/R2	_	_	0.09	0.1	0.11	

Marking

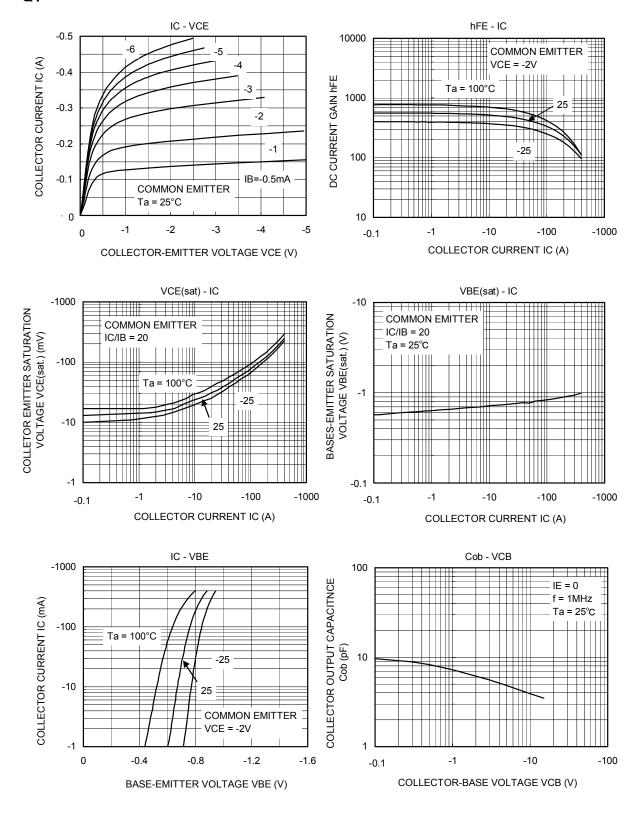


Equivalent Circuit (Top View)

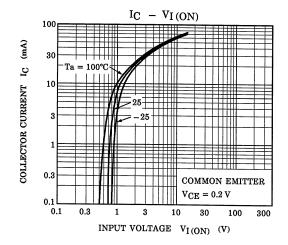


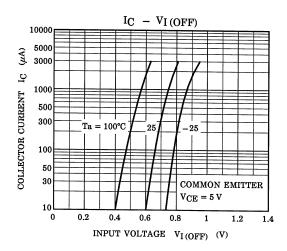
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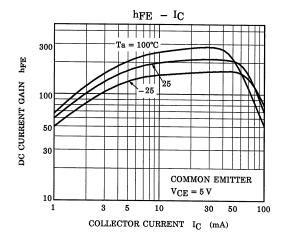
Q1

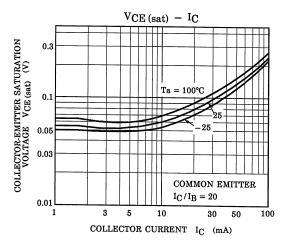


Q2

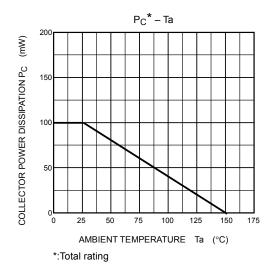








(Q1, Q2 common)



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